



*FIG. 1*

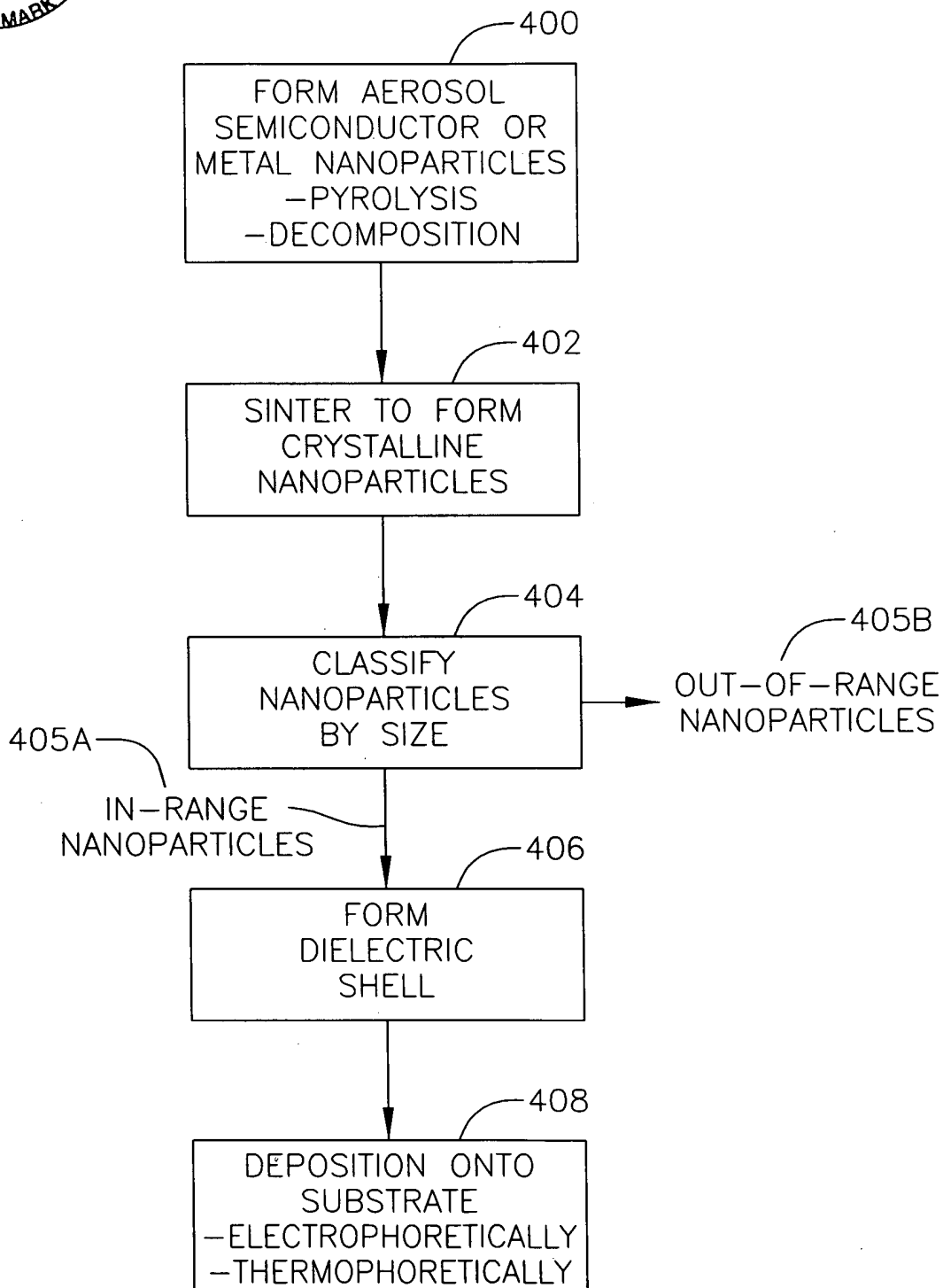
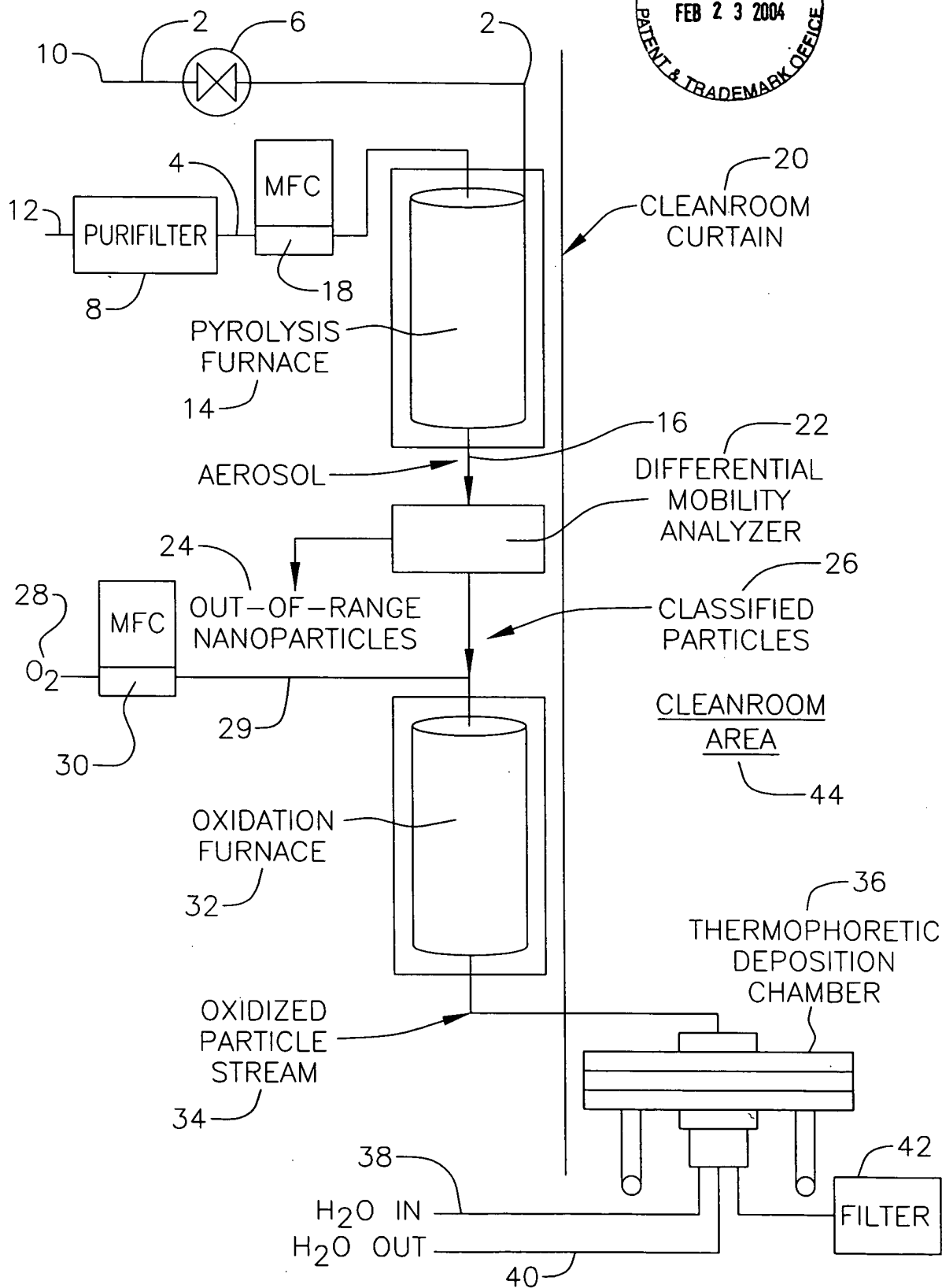
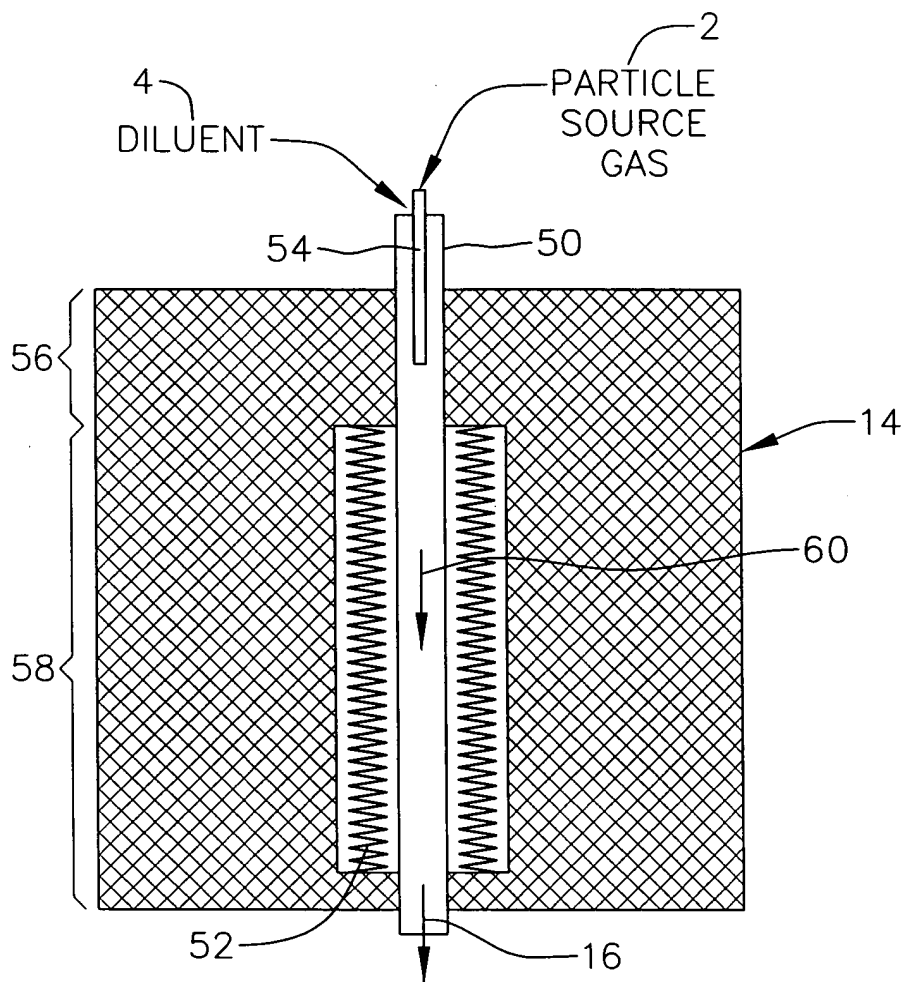


FIG. 2



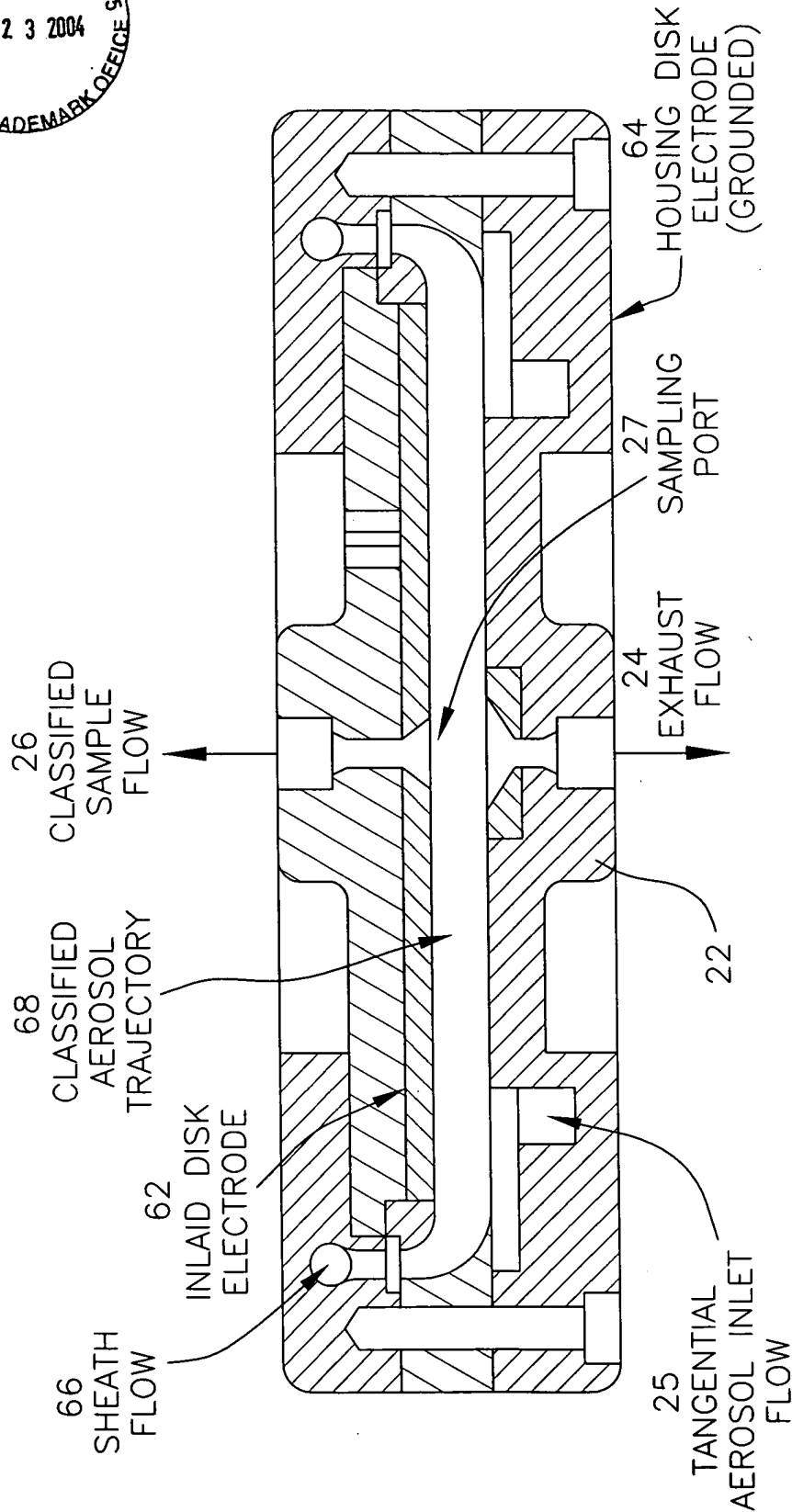


*FIG. 3*





**FIG. 4**



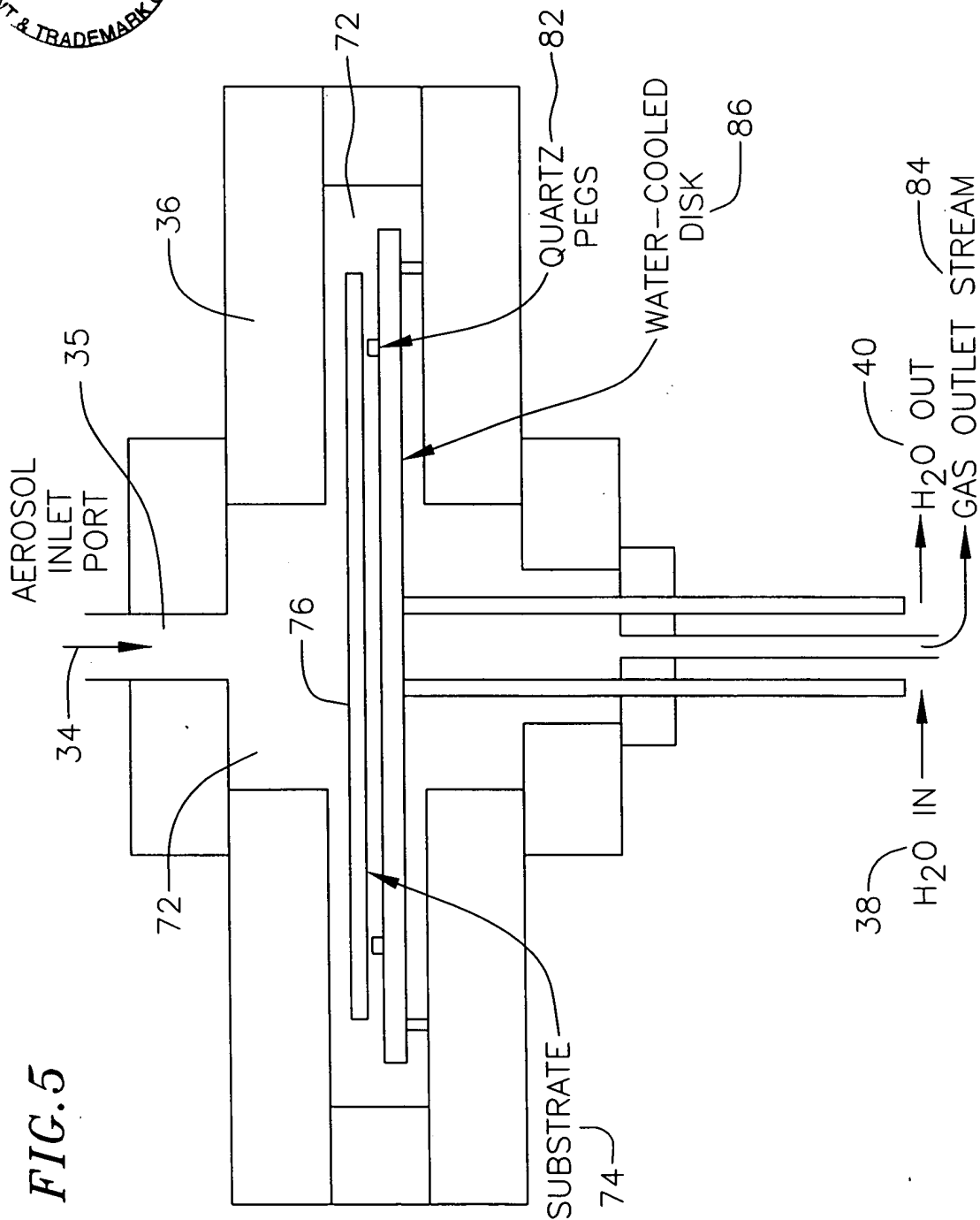


FIG. 6

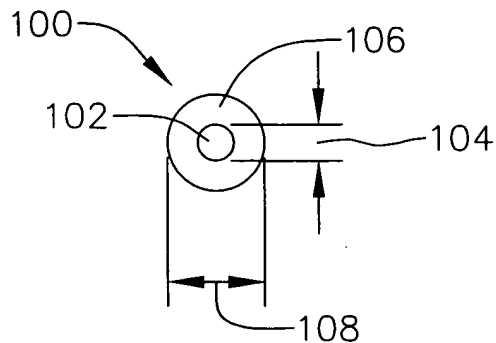


FIG. 7

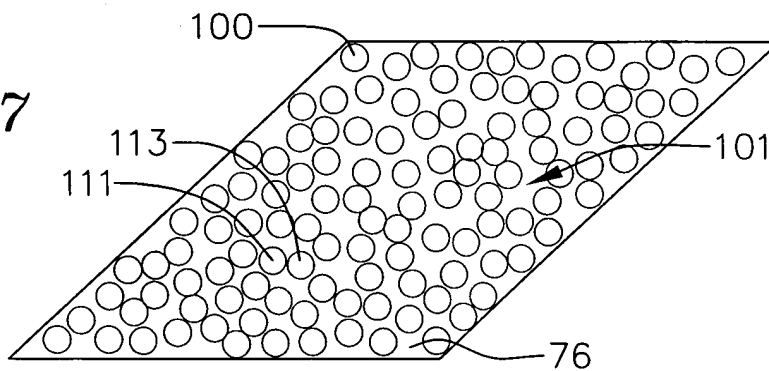


FIG. 8

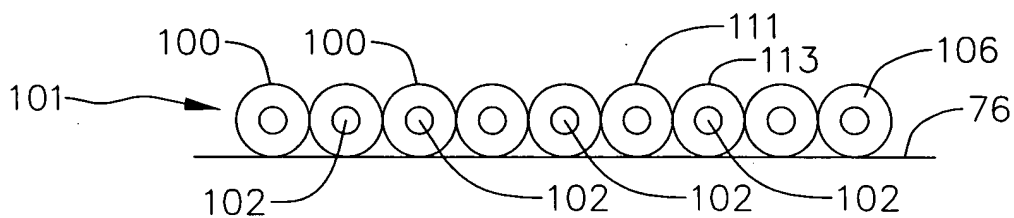


FIG. 9

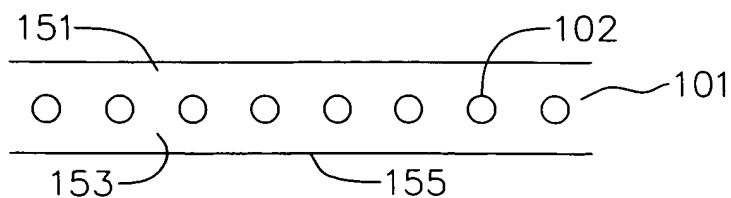




FIG. 10

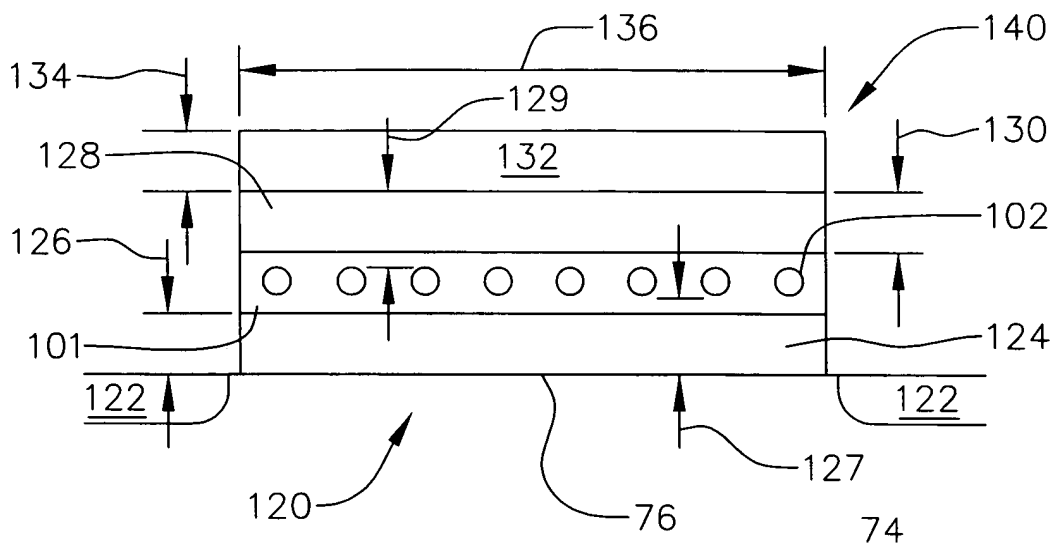


FIG. 11

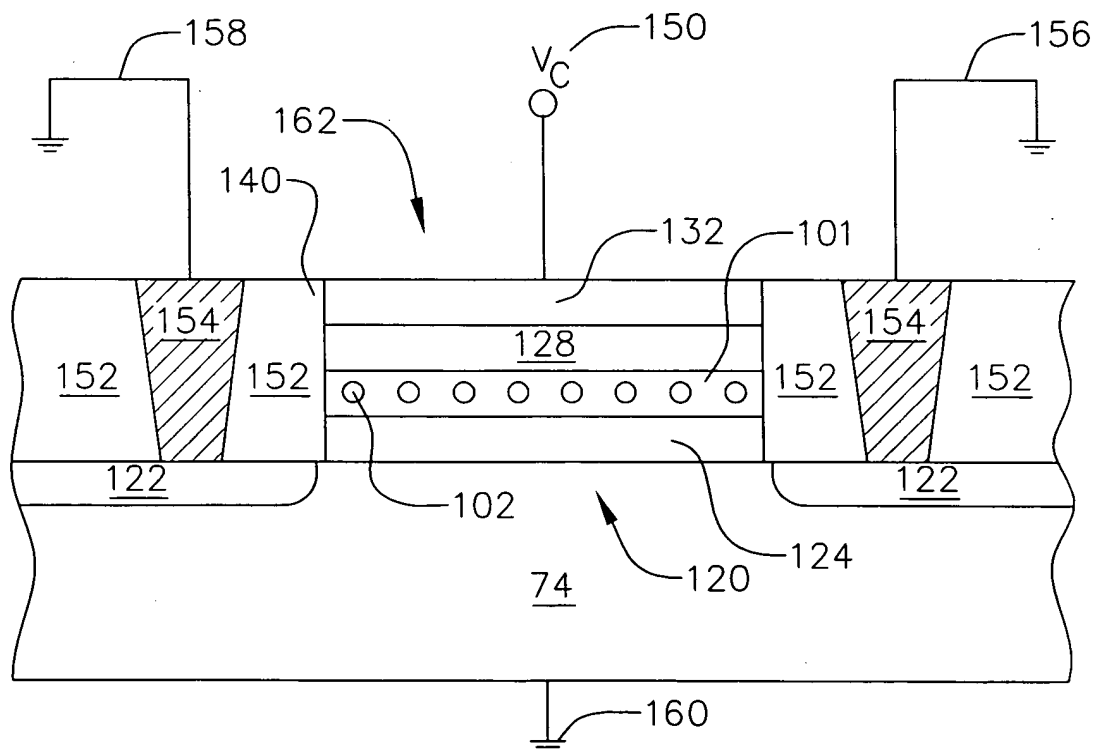
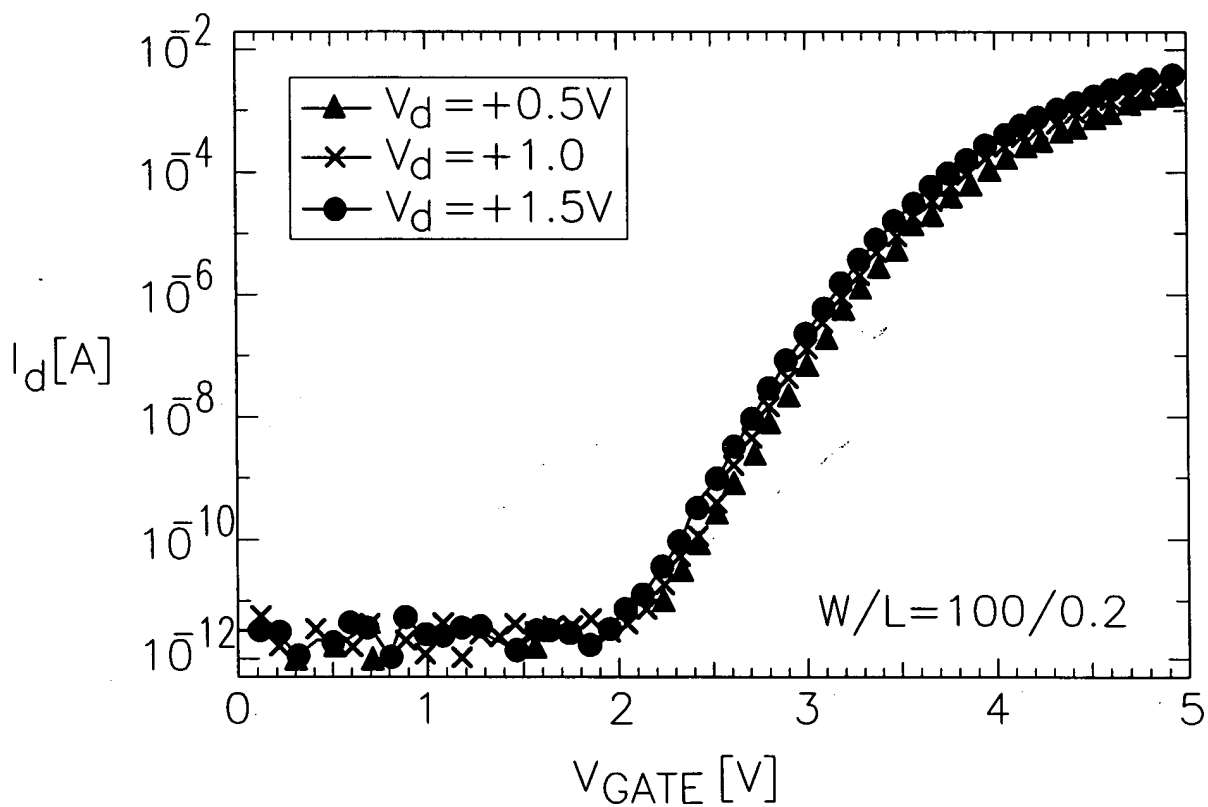


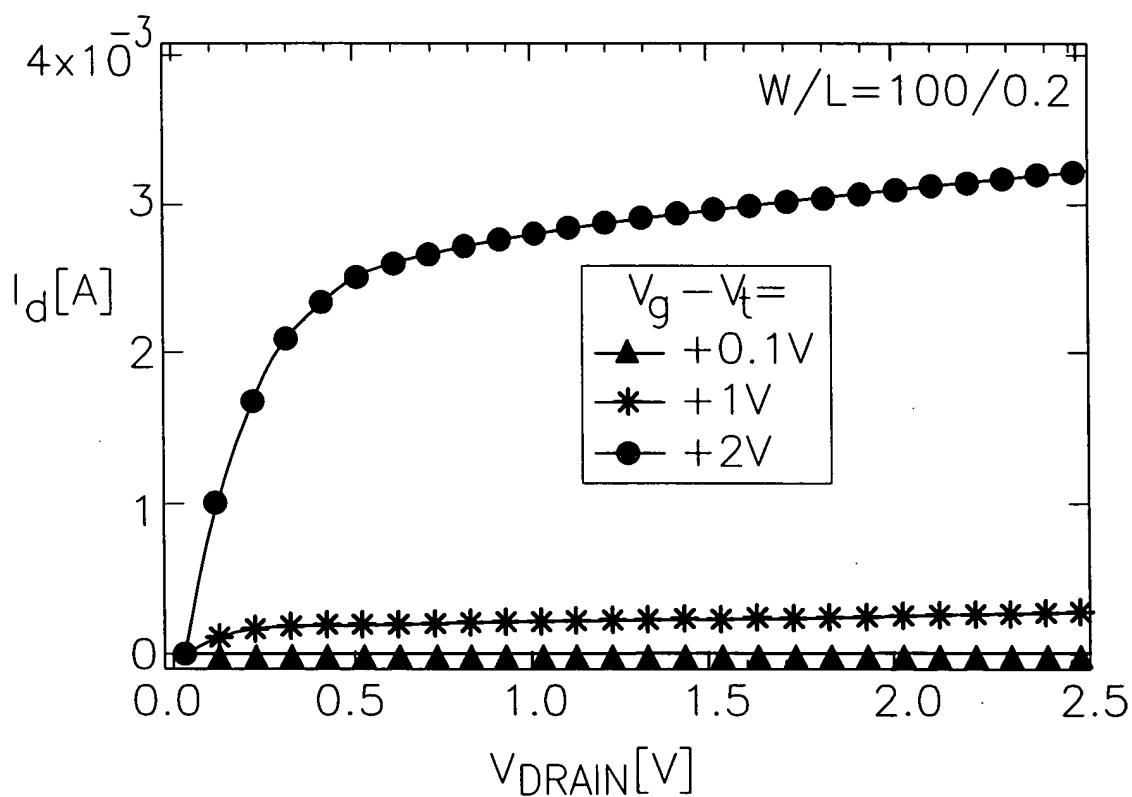


FIG. 12

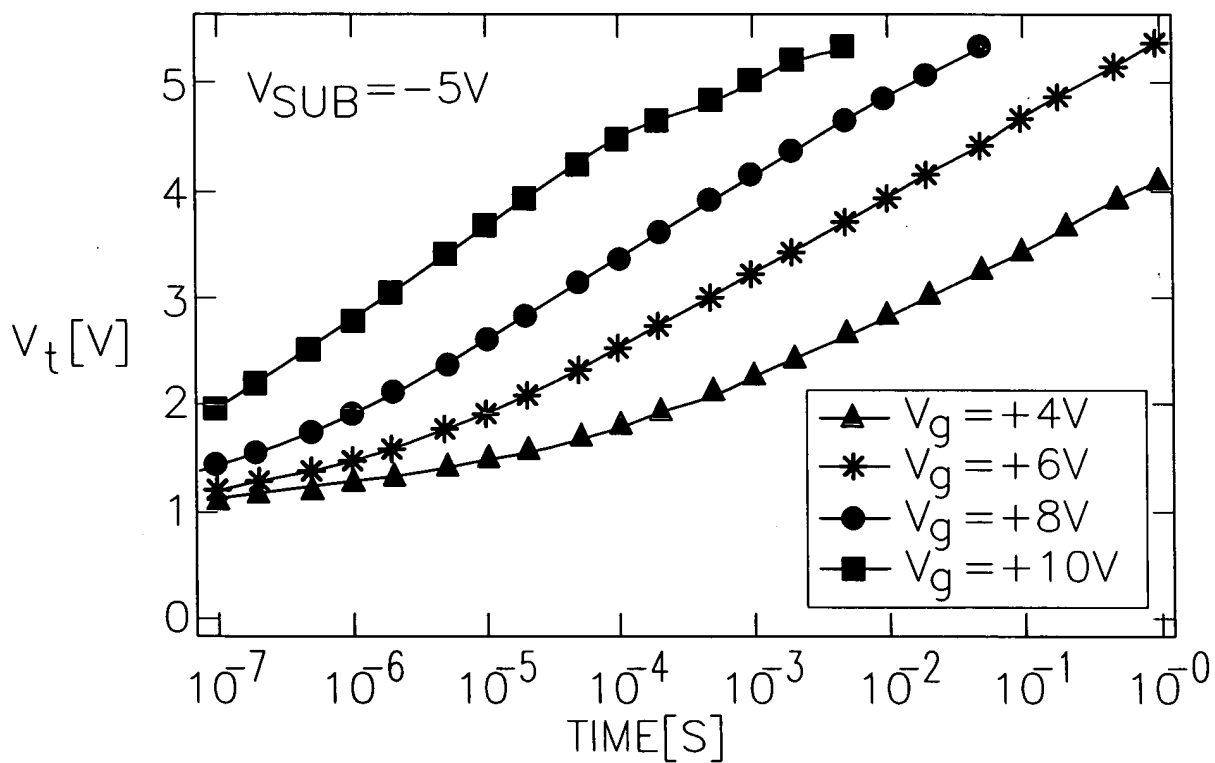


SUBTHRESHOLD CHARACTERISTICS OF A  $0.2\mu m$  n-TYPE AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET (SUBTHRESHOLD SLOPE=200mV/dec; DIBL=100mV/V).

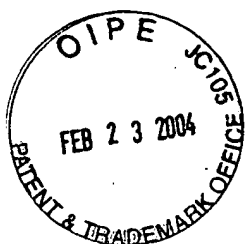
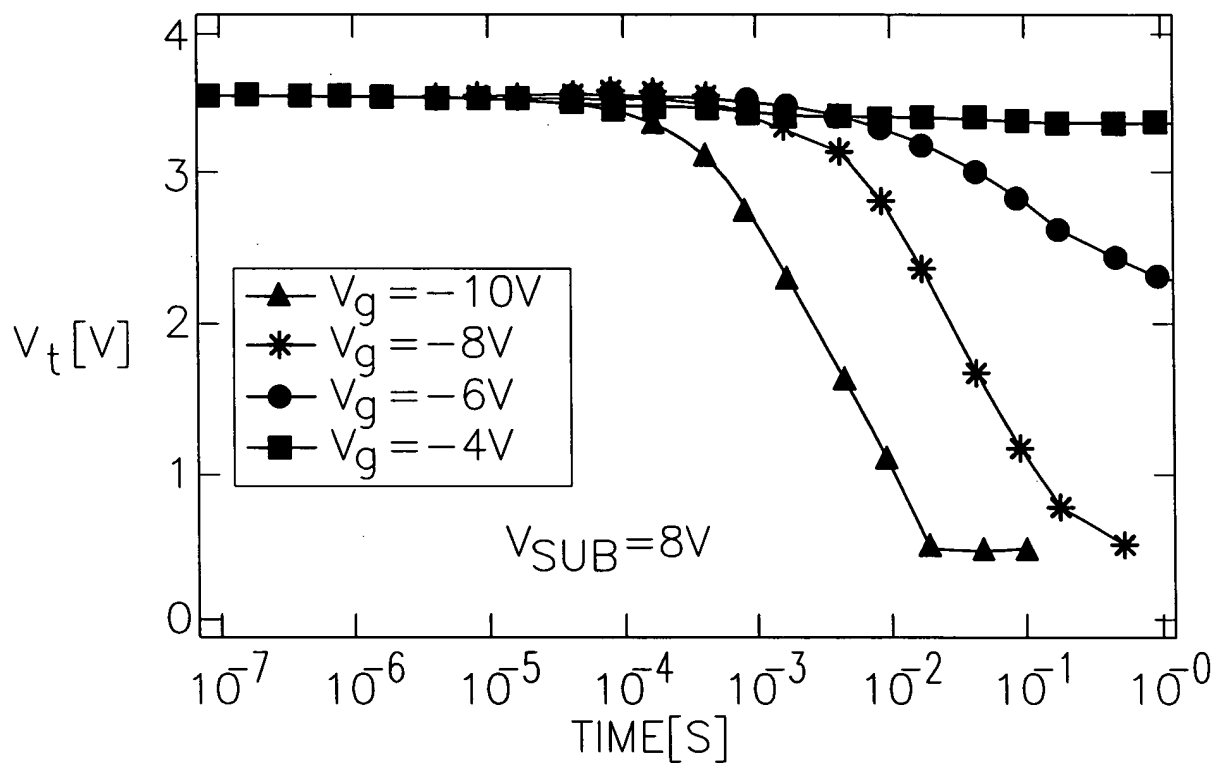


*FIG. 13*

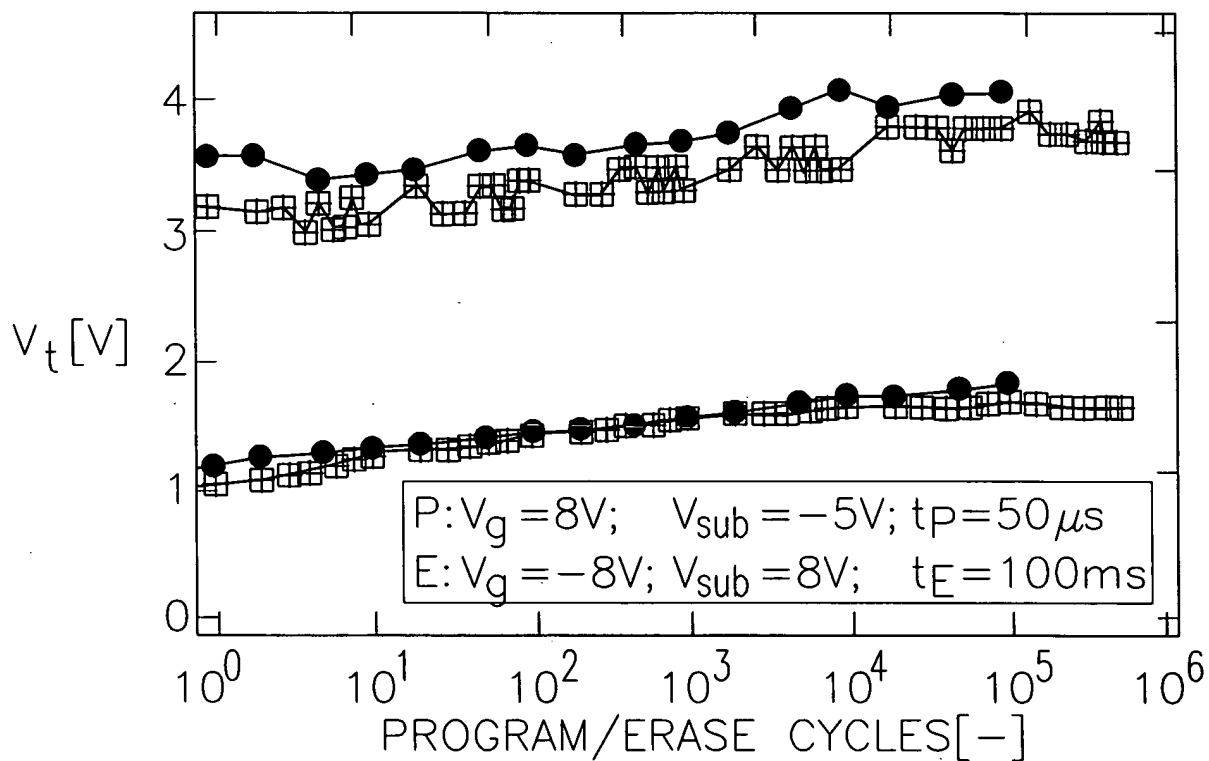
OUTPUT CHARACTERISTICS OF A  $0.2\mu m$   
AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET;  
DRIVE CURRENT =  $30\mu A/\mu m$

*FIG. 14*

PROGRAMMING TRANSIENTS (UNIFORM FN TUNNELING) OF THE NANOCRYSTAL NVM DEVICE.

*FIG. 15*

ERASE TRANSIENTS (UNIFORM FN TUNNELING).

*FIG. 16*

ENDURANCE CHARACTERISTIC; ONLY LIMITED WINDOW CLOSURE IS OBSERVED AFTER  $10^5$  PROGRAM/ERASE CYCLES.



FIG. 17

